HFZT

2SD886

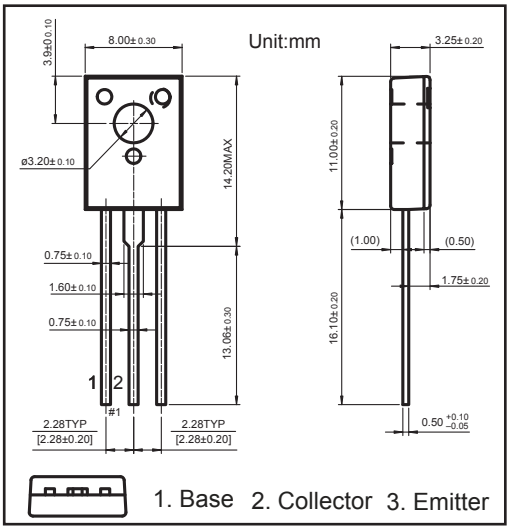
TO-126 Plastic-Encapsulate Transistors

FEATURES

- Low Voltage
- High Current
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3	A
Collector Power Dissipation	P_C	1	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	125	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 ~ +150	℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=5mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50V,I_E=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			1	μA
DC current gain	$h_{FE(1)}$*	V_{CE}=2V, I_C=20mA	100			
	$h_{FE(2)}$*	V_{CE}=2V, I_C=1A	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100μA,I_B=200mA			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=100μA,I_B=200mA			2	V
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0, f=1MHz		45		pF
Transition frequency	f_T	V_{CE}=5V, I_C=100mA		80		MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%